

Luttinger liquid behavior in single-wall nanotubes

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Transport properties of metallic single-wall nanotubes are examined based on the Luttinger liquid theory. Focusing on a nanotube transistor setup, the linear conductance is computed from the Kubo formula using perturbation theory in the lead-tube tunnel conductances. For sufficiently long nanotubes and high temperature, phonon backscattering should lead to an anomalous temperature dependence of the resistivity.

Carbon nanotubes possess many fascinating properties and have recently attracted a lot of attention. Metallic nanotubes can behave as ballistic quantum wires over lengths of several μm [1] and hence constitute perfect experimental realizations of 1D conductors. It is now well-known that Fermi liquid theory must break down in such a 1D conductor because of the Coulomb interactions among the electrons. In fact, at temperatures above the milli-Kelvin range, an individual metallic single-wall nanotube (SWNT) can be accurately described in terms of Luttinger liquid (LL) theory [2]. The LL is a prototypical yet simple model for non-Fermi liquid behavior. The interaction strength is measured in terms of a single parameter $g \leq 1$, where $g = 1$ is the noninteracting limit. For a SWNT, the theoretical estimate is [2] $g \simeq \{1 + (8e^2/\pi\hbar\epsilon v_F) \ln(L/2\pi R)\}^{-1/2}$, where the only logarithmic dependence on the tube length $L \approx 1 \mu\text{m}$ and the radius $R \approx 1.4 \text{ nm}$ leads to a value around $g \approx 0.2$ to 0.3 . Here, ϵ is the background dielectric constant and $v_F \approx 8 \times 10^5 \text{ m/s}$ is the Fermi velocity. The LL should also show up in a variety of other systems, such as long chain molecules, the edge states in a fractional quantum Hall bar, or in single-channel quantum wires in semiconductor heterostructures. Unfortunately, despite of many efforts, a generally accepted experimental realization of the LL in these systems is still lacking. For a nanotube rope, however, transport experiments have recently been reported that provide clear evidence for a LL [3]. A rope should show LL behavior if three conditions are met: (a) only one metallic tube is contacted by the leads, (b) most tubes in the rope are not metallic, and (c) electron tunneling between different metallic tubes in the rope can be neglected.

Let us consider a transistor consisting of a tube of length L , where contact to external leads is established at positions $0 < x_1 < x_2 < L$. The leads $i = 1, 2$ are

modelled by free electrons, and we take the standard tunneling Hamiltonian for the lead-tube couplings. We assume pointlike contacts and focus on the linear dc conductance, which, according to the Kubo formula, takes the form

$$G = \lim_{\omega \rightarrow 0} \frac{1}{\hbar\omega} \text{Im} \left[\int_0^{\hbar\beta} d\tau \exp(i\Omega\tau) \langle I^{(1)}(\tau) I^{(2)}(0) \rangle \right]_{i\Omega \rightarrow \omega + i\delta}, \quad (1)$$

where $\beta = 1/k_B T$. Since the dc current through both contacts coincides, we may take an arbitrary linear combination $I^{(1)} = \epsilon_1 I_1 + \epsilon_2 I_2$ [where $\epsilon_1 + \epsilon_2 = 1$] of the currents I_1 and I_2 through the tunnel contacts at x_1 and x_2 , respectively. Since the transport voltage can also be split up arbitrarily [4], the second current operator can be written as $I^{(2)} = \kappa_1 I_1 + \kappa_2 I_2$ with $\kappa_1 + \kappa_2 = 1$. This gives

$$G = \sum_{ij=1,2} \epsilon_i \kappa_j G_{ij}, \quad (2)$$

where the matrix elements G_{ij} directly follow from Eq. (1). We compute these matrix elements by perturbation theory in the dimensionless bare tunnel conductances $g_i = R_K/R_{T,i}$ with the resistance quantum $R_K = h/e^2$ and the tunnel resistance $R_{T,i}$ through contact $i = 1, 2$. Under an exact calculation, one could use any choice for ϵ_1 and κ_1 in Eq. (2) [4]. Under a perturbative calculation for the G_{ij} , however, requiring independence of ϵ_1 and κ_1 is equivalent to maximizing Eq. (2) with respect to these parameters and gives $\epsilon_1 = (G_{21} + G_{22})/\sum_{ij} G_{ij}$ and $\kappa_1 = (G_{12} + G_{22})/\sum_{ij} G_{ij}$. The lowest-order result in g_i follows from the expansion $G_{ii} = G_i + \delta G_{ii}$, where δG_{ii} as well as G_{12} and G_{21} are of at least second order in (g_1, g_2) but G_i is of first order. Then Eq. (2) leads to

$$G = \frac{G_1 G_2}{G_1 + G_2}. \quad (3)$$

This formula describes sequential incoherent transport through the device and is appropriate for high temperatures, where $k_B T$ exceeds the charging energy $E_c \approx e^2 \ln(L/R)/\epsilon L$. In addition, the condition $\hbar v_F/k_B T \ll |x_2 - x_1|$ should hold. On the other hand, at lower temperatures coherent processes such as co-tunneling play a prominent role and lead to the breakdown of Eq. (3). From the general expression (2) we observe that $G \approx G_{12}/2$, since G_i vanishes as $T \rightarrow 0$ unless one has a resonance. This is consistent with the results of Ref. [5] for transport through a LL ring but at the same time indicates that the latter are only valid for thermal energies $k_B T$ well below the charging energy E_c . Therefore the “straightforward” application of the Kubo formula to such problems is not as simple as commonly thought.

Let us start with the high-temperature limit. Perturbation theory yields with $G_0 = 4e^2/h$ and the Fourier transformed LL Greens function $K(x_i, \xi)$ at equal sites,

$$G_i/G_0 = -\pi g_i \int d\xi (-dn_F(\xi)/d\xi) \text{Im} K(x_i, \xi). \quad (4)$$

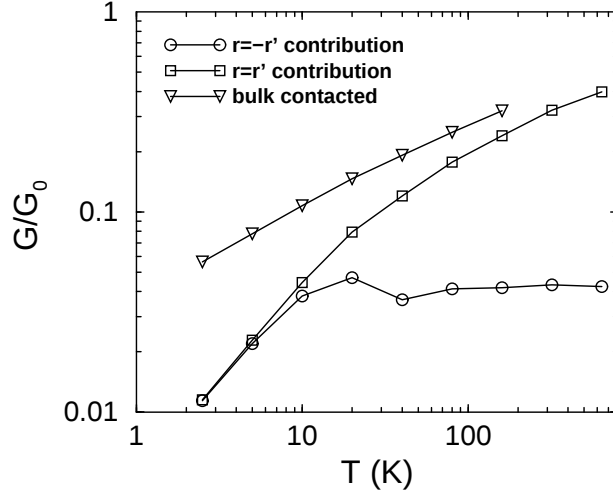


Figure 1: High-temperature conductance (3) for $g = 0.2$, $g_1 = g_2 = 0.1$ and $L = 10^4 a = 2.46 \mu\text{m}$. Note the double-logarithmic scales. For the bulk- (end-) contacted case, $x_1 = L - x_2 = 3500a$ ($5a$). For the end-contacted case, the $r = r'$ and $r = -r'$ contributions are plotted separately.

The derivative of the Fermi function is $-dn_F(\xi)/d\xi = (4k_B T)^{-1} \cosh^{-2}[\xi/2k_B T]$. Technically speaking, $K(x_i, \xi)$ is obtained from a decomposition of the electron operator into 1D fermions $\psi_{r,\alpha,\sigma}$, where $r = \pm$ is the right- or left-moving part, $\alpha = \pm$ denotes the right or left Fermi point, and $\sigma = \pm$ is the spin index, and subsequent use of the bosonization method [2]. Eq. (4) shows that the conductance is related to the local tunneling density of states of the LL. The respective power laws are well-known [2], $G_i \propto T^\eta$, where the exponent η is given by $\eta_b = (g^{-1} + g - 2)/8$ for tunneling into the bulk, i.e., far away from the ends of the tube, and the end exponent is $\eta_e = (g^{-1} - 1)/4$, see Figure 1. These predictions have been verified in recent experiments [3]. For the bulk-contacted case, the slope coincides with the correct value $\eta_b = 0.4$ for $g = 0.2$. For the end-contacted case, the slope is close to the end value $\eta_e = 1.0$ for low temperatures, but exhibits a crossover to the smaller bulk exponent around $T \approx 50$ K. This can be rationalized by separately looking at the $r = r'$ and $r = -r'$ contributions to the conductance. Mixing of right- and left-movers ($r = -r'$) violates momentum conservation and is only allowed close to the end. Due to thermal decorrelation such processes are destroyed with increasing temperature.

For $k_B T \ll E_c$, we compute the conductance as $G_{12}/2$. Following Ref. [5], we employ the Wick theorem. Although strictly speaking this is not correct, at sufficiently low temperatures the corresponding errors in G are expected to become very small. The gate-voltage dependence of the conductance is shown in Fig. 2. Due to the Coulomb blockade, one finds characteristic peaks. Their lineshape accurately follows the standard $\cosh^{-2}(\Delta V_G/2k_B T)$ form, and also the temperature depen-

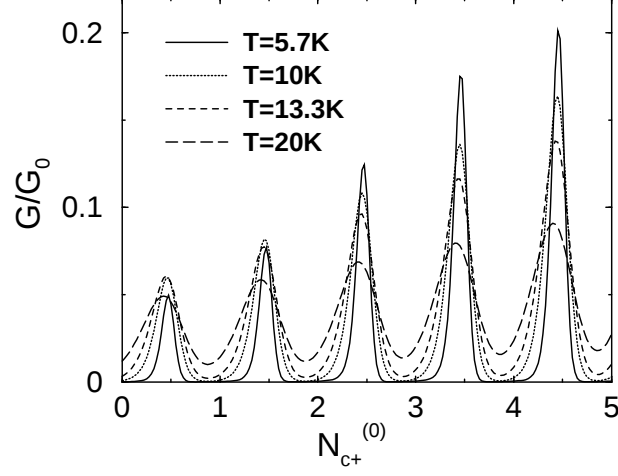


Figure 2: Low-temperature conductance $G = G_{12}/2$ as a function of the gate voltage $V_G \propto N_{c+}^{(0)}$ for $g = 0.2, g_1 = g_2 = 0.1, L = 10^4 a$ and $x_1 = L - x_2 = 0.1L$.

dence of the peak heights is in agreement with conventional Coulomb blockade theory.

In the remainder, we investigate the effect of *phonon backscattering* on the SWNT conductance. In most other systems where LL behavior is thought to be present phonon backscattering does not play an important role for transport properties because of the large momentum transfer $2k_F$. However, in a SWNT the relevant momentum transfer is $2q_F$, where $q_F \ll k_F$ is tuned by the gate voltage. Thermal population of phonon modes is then much more significant. The only low-energy phonons that couple right- and left-movers are the acoustic torsional modes with dispersion $\Omega(q) = v_t|q|$, where $v_t \approx 1.4 \times 10^4$ m/s. Following Ref. [6], the electron-phonon coupling is

$$H_{e-p} = \lambda \int dx \vartheta(x) \sum_{\alpha\sigma} \left(\psi_{+, \alpha, \sigma}^\dagger \psi_{-, \alpha, \sigma} + \text{H.c.} \right), \quad (5)$$

with $\lambda \simeq n \times 2.92$ eVÅ for a (n, n) tube. Using the bosonization method to describe the electronic degrees of freedom $\psi_{r, \alpha, \sigma}$, we focus on the lowest-order ($\propto \lambda^2$) contribution $\delta G_p(T)$ to $G(T)$. The phonon field $\vartheta(x)$ can be expressed in terms of free boson operators a_q . Since $v_t \ll v_F$, we can safely neglect the time-dependence of a_q , and hence the phonon averaging simply produces a boson mode occupation factor $\coth[\hbar\beta\Omega(q)/2]$. Furthermore, for exactly the same reason, this factor can be approximated by $2/\hbar\beta v_t|q|$, and we obtain

$$\delta G_p(T)/G_0 = -L \frac{\gamma_g \lambda^2}{a C_t v_F} (\pi a k_B T / v_F)^{(1+g)/2}, \quad (6)$$

with the twist modulus $C_t \simeq n^3 \times 18$ eVÅ [6] and the numerical prefactor $\gamma_g = 4\pi^{-2} g^{1+g/2} \sin[\pi(3+g)/4] \int_0^\infty dz z / \sinh^{(3+g)/2}(z)$. For example, $\gamma_1 = 2/\pi$ and $\gamma_{0.2} \simeq$

0.112. The tube length L appearing in Eq. (6) should be replaced by $|x_2 - x_1|$ if the phonon modes can be pinned at the locations of the tube-lead contacts. Further modifications might be necessary if strong interactions with the substrate influence the phonon dynamics.

To convert Eq. (6) into a resistivity, we note that $G \equiv G_0 \tilde{g} = G_0 + \delta G_p$ is the two-terminal conductance of a nanotube in adiabatic contact to voltage sources. The resistivity is obtained from the four-terminal conductance $\tilde{G} = G_0 \tilde{g}/(1 - \tilde{g})$, so that the 1D relation $\tilde{G} = \sigma/L$ with $\rho = 1/\sigma$ yields the 1D resistivity due to phonon backscattering

$$\rho = \frac{h}{4e^2} \frac{\gamma_g \lambda^2}{a C_t v_F} (\pi a k_B T / v_F)^{(1+g)/2}. \quad (7)$$

For $g = 1$, Eq. (7) agrees with the theory for uncorrelated electrons and the corresponding experimental results found in many-rope systems and mats [6]. For an individual SWNT, the long-ranged Coulomb interactions among the electrons change this into an anomalous $\rho \sim T^{(1+g)/2}$ power law. It is apparent from Eq. (6) that the conductance will be dominated by phonon backscattering at sufficiently high temperatures, $T > T_g^*(L)$. Let us therefore estimate T^* employing the *ad hoc* criterion $|\delta G_p|/G_0 = \nu$ with, say, $\nu = 0.1$. This gives

$$T_g^*(L) \approx 8000 \left(\frac{3560 \gamma_g}{n} L \right)^{-2/(1+g)}, \quad (8)$$

where T^* is measured in Kelvin and L in μm . Putting $n = 10$ and $g = 1$, this gives $T^* = 180$ K for a $L = 200$ nm tube, and $T^* = 35$ K for a $L = 1\mu\text{m}$ tube. For strongly correlated electrons, the length dependence is even more dramatic. Putting $g = 0.2$ and again $n = 10$, for a $L = 200$ nm tube we get $T^* = 250$ K, while for a $L = 1\mu\text{m}$ tube, phonons already begin to dominate above $T^* = 17$ K.

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References

- [1] S.J. Tans *et al.*, Nature **386**, 474 (1997); **394**, 761 (1998).
- [2] R. Egger and A.O. Gogolin, Phys. Rev. Lett. **79**, 5082 (1997); Eur. Phys. J. B **3**, 281 (1998); C.L. Kane *et al.*, Phys. Rev. Lett. **79**, 5086 (1997).
- [3] M. Bockrath *et al.*, Nature **397**, 598 (1999).
- [4] G. Göppert and H. Grabert, Phys. Rev. B **58**, R10155 (1998).
- [5] J.M. Kinaret *et al.*, Phys. Rev. B **57**, 3777 (1998).
- [6] C.L. Kane *et al.*, Europhys. Lett. **41**, 683 (1998).